

MOSFETs Silicon 100V N-Channel MOS
■ Applications

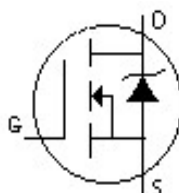
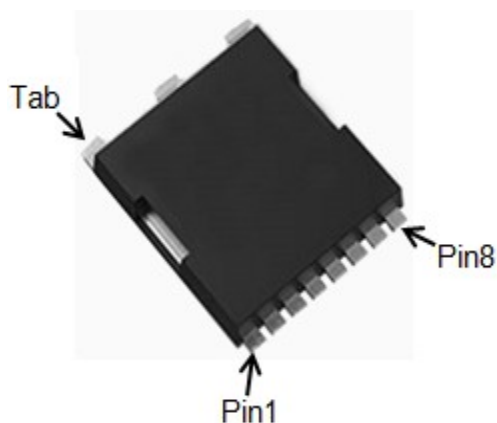
- Synchronus Rectification
- Industrial and Motor Drive
- DC/DC and AC/DC Converters
- Power Tools
- BMS

■ Features

- High-Speed Switching
- Low $R_{DS(ON)}$
- Low Gate Charge
- RoHS and Halogen-Free Compliant
- 100% UIS and RG Tested

■ Product Summary

V_{DS}	100	V
I_D	425	A
$R_{DS(ON)}, Typ@10V$	1.0	m Ω
Q_g	188	nC


TOLL

Gate: Pin1
 Drain: Tab
 Source: Pin2~8

Marking	Package	Packaging	Min. package quantity
MT1D3R100SH	TOLL	Tape & Reel	2000



■ Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current Tc=25°C (Note 1)	I_D	425	A
Continuous Drain Current Tc=100°C (Note 1)		300	A
Drain Current-Pulsed (Note 1)	I_{DM}	1500	A
Total Dissipation	P_D	469	W
Junction Temperature	T_j	175	°C
Storage Temperature	T_{stg}	-55-175	°C
Single Pulse Avalanche Energy (Note 2)	E_{AS}	2400	mJ

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

■ Thermal Characteristics

Parameter	Symbol	Max	Unit
Maximum Junction-to-Case	$R_{\theta JC}$	0.32	°C/W
Maximum Junction-to-Ambient	$R_{\theta JA}$	40	°C/W

Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2: $V_{DD}=50V$, $T_{ch}=25^{\circ}C$ (initial), $L=0.5mH$, $R_g=25\Omega$.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



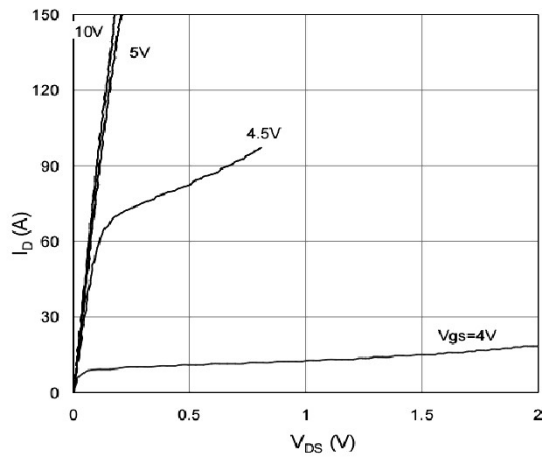
■ Electrical Characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Static Parameters							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA		100	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V		-	-	1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V		-	-	±100	nA
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA		2.0	3.2	4.0	V
Drain-Source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A		-	1.0	1.2	mΩ
			Tj=125℃	-	1.8	-	
Dynamic Characteristics							
Input Capacitance	C _{iss}	V _{DS} =35V, V _{GS} =0V, f=1.0MHz		-	13170	-	pF
Output Capacitance	C _{oss}			-	6460	-	pF
Reverse Transfer Capacitance	C _{rss}			-	200	-	pF
Gate Resistance	R _g	V _{DS} =0V, V _{GS} =0V, f=1.0MHz		-	3.6	-	Ω
Switching Paramters							
Turn-On Delay Time	t _{d(on)}	V _{DS} =50V, I _D =100A, V _{GS} =10V, R _G =3Ω		-	30	-	ns
Turn-On Rise Time	t _r			-	78	-	ns
Turn-Off Delay Time	t _{d(off)}			-	95	-	ns
Turn-Off Rise Time	t _f			-	35	-	ns
Total Gate Charge	Q _g	V _{DS} =50V, I _D =20A, V _{GS} =10V		-	188	-	nC
Gate-Source Charge	Q _{gs}			-	61	-	nC
Gate-Drain Charge	Q _{gd}			-	40	-	nC
Source-Drain Characteristics							
Diode Forward Voltage	V _{sd}	V _{GS} =0V, IF=10A		-	0.75	1.2	V
Reverse Recovery Time	t _{rr}	V _R =50V, I _F =20A, di/dt=100A/us		-	136	-	ns
Reverse Recovery Charge	Q _{rr}			-	420	-	nC

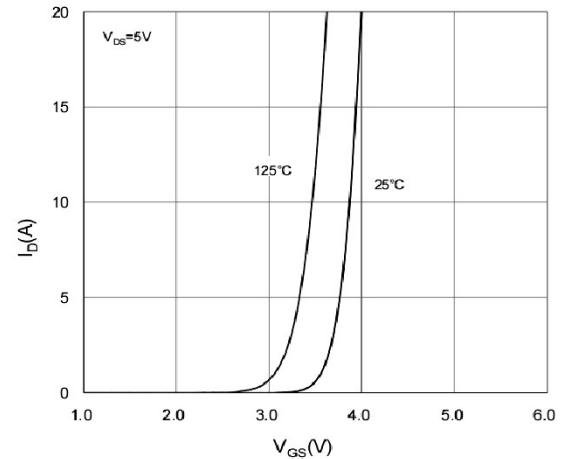




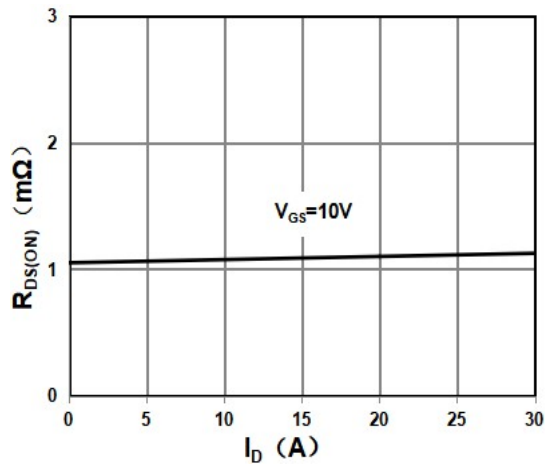
■ Characteristics Curves



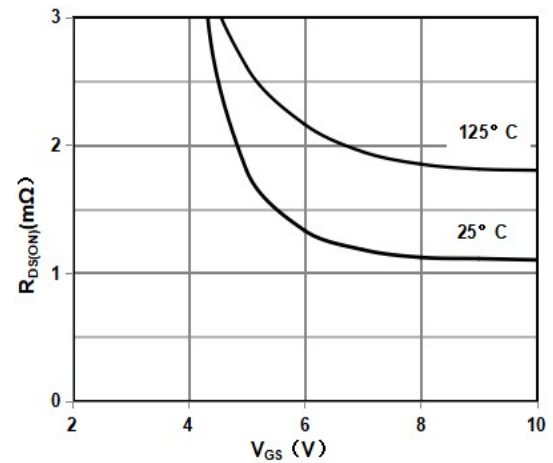
Output Characteristics



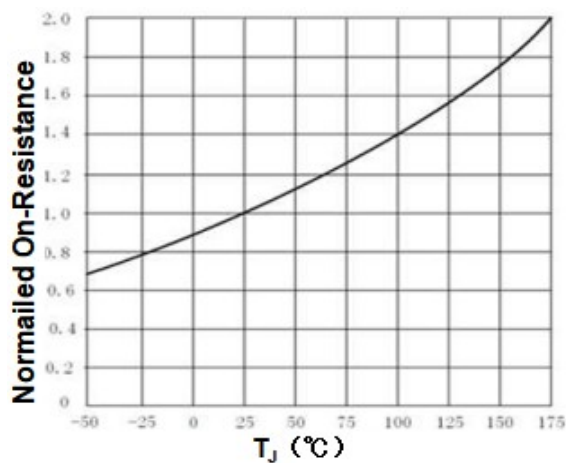
Transfer Characteristics



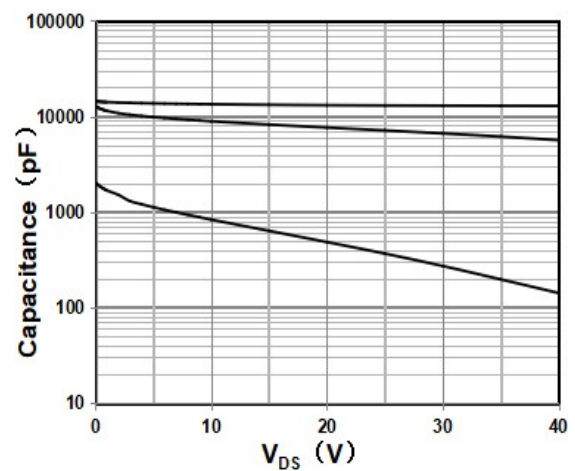
On Resistance Vs Drain Current



On Resistance Vs Gate Source Voltage

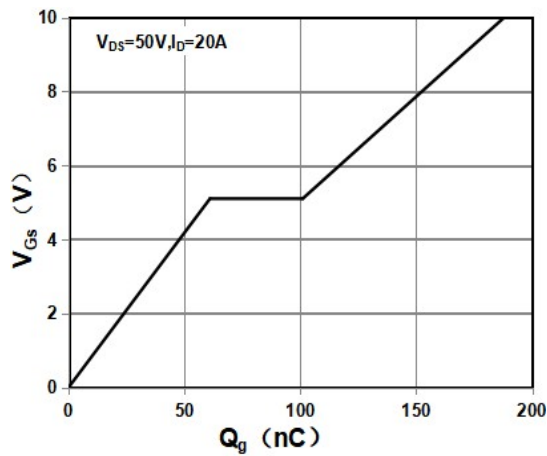


Rdson-JunctionTemperature

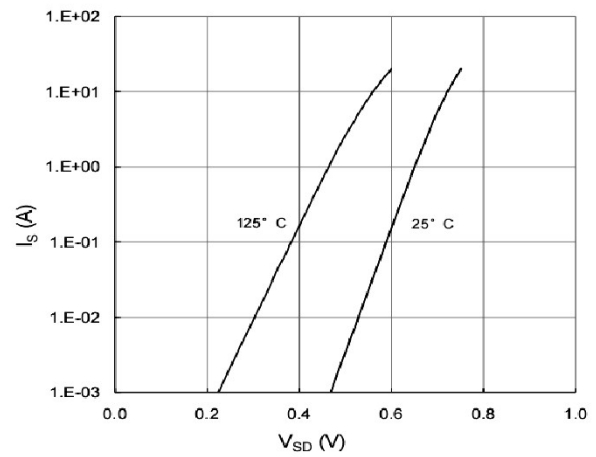


Capacitance

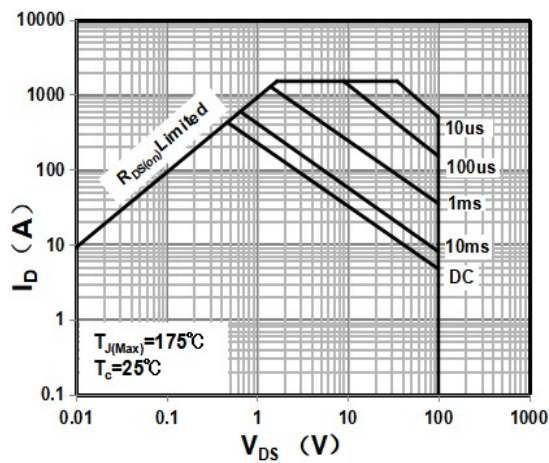




Gate Charge Waveform



Source-Drain Diode Forward Voltage



Maximum Safe Operating Area

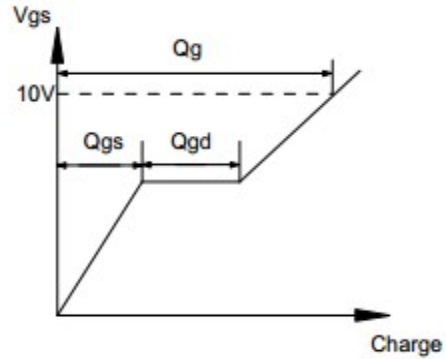
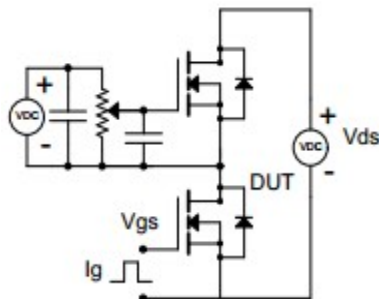
Note : The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



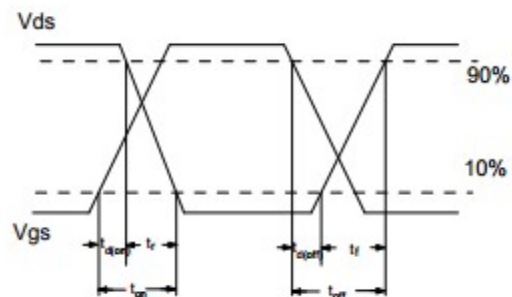
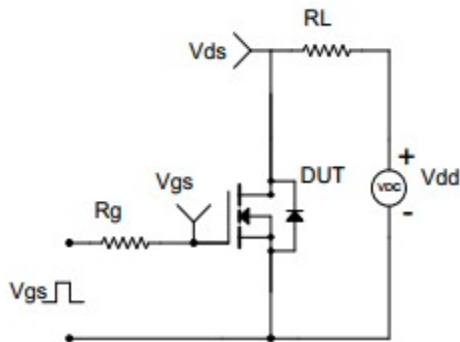


■ Test Circuit & Waveform

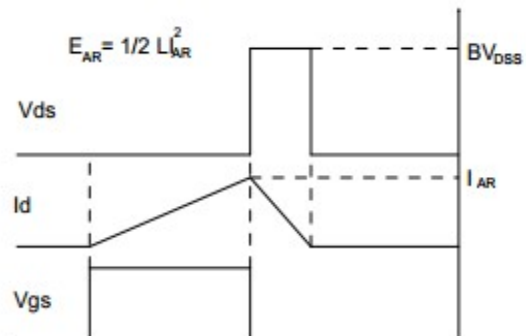
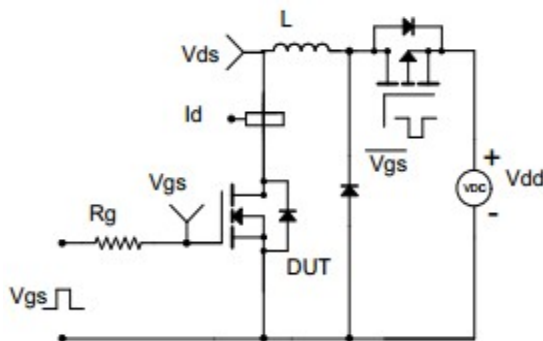
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveform



**■ TOLL Package Dimensions**

Unit: mm

Symbol	Min	Nom	Max	Symbol	Min	Nom	Max
A	2.25	2.3	2.35	e1		1.225	
A1	1.75	1.8	1.85	E	9.85	9.9	9.95
b	0.65	0.7	0.75	E1	8	8.1	8.2
b1	9.75	9.8	9.85	H	11.6	11.7	11.8
b2	0.7	0.75	0.8	H1		6.95	
c	0.45	0.5	0.55	K		3.1	
D	10.35	10.4	10.45	L	1.55	1.65	1.75
D1	11	11.1	11.2	L1	0.65	0.7	0.75
D2	3.25	3.3	3.35	L2	0.5	0.6	0.7
D4	4.5	4.55	4.6	Q		7.95	
e		1.2		θ		10°	

